PD - 95629

International
IOR Rectifier

IRFB17N60KPbF

SMPS MOSFET

HEXFET® Power MOSFET

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits
- Lead-Free

V_{DSS}	$R_{DS(on)}$ typ.	I_D
600V	**0.35Ω**	**17A**

Benefits

- Smaller TO-220 Package
- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamicdv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current

TO-220AB

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	17	
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	11	A
I_{DM}	Pulsed Drain Current ①	68	
P_D @T_C = 25°C	Power Dissipation	340	W
	Linear Derating Factor	2.7	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	11	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	°C
	Mounting Torque, 6-32 or M3 screw	10	N

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	---	330	mJ
I_{AR}	Avalanche Current①	---	17	A
E_{AR}	Repetitive Avalanche Energy①	---	34	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	0.37	
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	---	°C/W
$R_{\theta JA}$	Junction-to-Ambient	---	58	

8/4/04

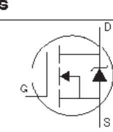
Static @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	600	–––	–––	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.60	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	0.35	0.42	Ω	V_{GS} = 10V, I_D = 10A ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	–––	5.0	V	V_{DS} = V_{GS}, I_D = 250μA
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	50	μA	V_{DS} = 600V, V_{GS} = 0V
		–––	–––	250	μA	V_{DS} = 480V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 30V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -30V

Dynamic @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	5.9	–––	–––	S	V_{DS} = 50V, I_D = 10A
Q_g	Total Gate Charge	–––	–––	99	nC	I_D = 17A
Q_{gs}	Gate-to-Source Charge	–––	–––	32		V_{DS} = 480V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	47		V_{GS} = 10V, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	–––	25	–––	ns	V_{DD} = 300V
t_r	Rise Time	–––	82	–––		I_D = 17A
$t_{d(off)}$	Turn-Off Delay Time	–––	38	–––		R_G = 7.5Ω
t_f	Fall Time	–––	32	–––		V_{GS} = 10V,See Fig. 10 ④
C_{iss}	Input Capacitance	–––	2700	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	240	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	21	–––		f = 1.0MHz, See Fig. 5
C_{oss}	Output Capacitance	–––	2950	–––		V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	–––	67	–––		V_{GS} = 0V, V_{DS} = 480V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance	–––	120	–––		V_{GS} = 0V, V_{DS} = 0V to 480V ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	17	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	68		
V_{SD}	Diode Forward Voltage	–––	–––	1.5	V	T_J = 25°C, I_S = 17A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	520	780	ns	T_J = 25°C, I_F = 17A
Q_{rr}	Reverse RecoveryCharge	–––	5620	8430	nC	di/dt = 100A/μs ④
t_{rr}	Reverse Recovery Time	–––	580	870	ns	T_J = 125°C, I_F = 17A
Q_{rr}	Reverse RecoveryCharge	–––	6470	9700	nC	di/dt = 100A/μs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting T_J = 25°C, L = 2.3mH, R_G = 25Ω, I_{AS} = 17A,

③ I_{SD} ≤ 17A, di/dt ≤ 380A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

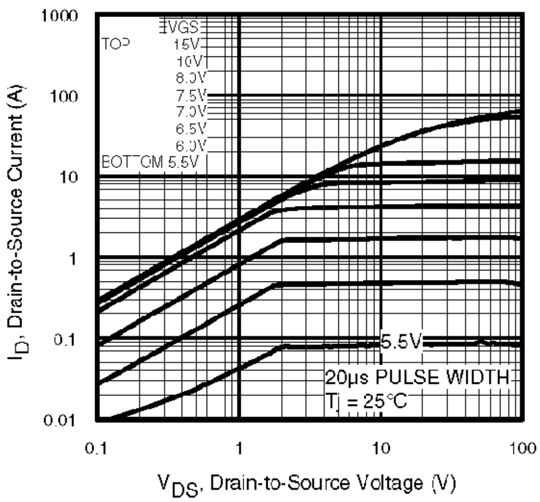


Fig 1. Typical Output Characteristics

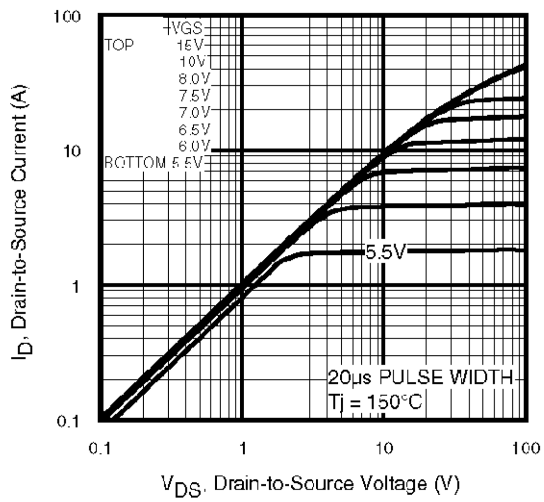


Fig 2. Typical Output Characteristics

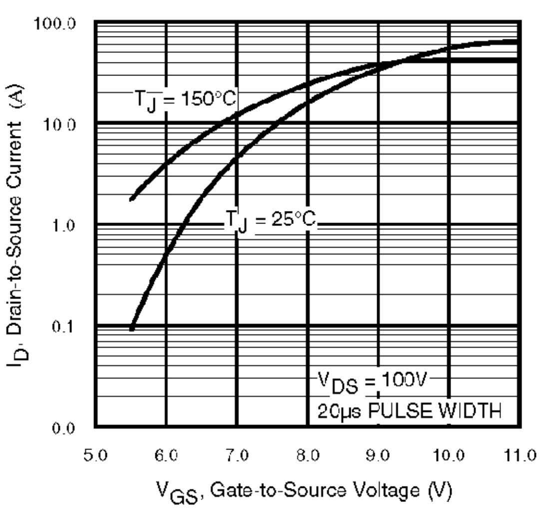


Fig 3. Typical Transfer Characteristics

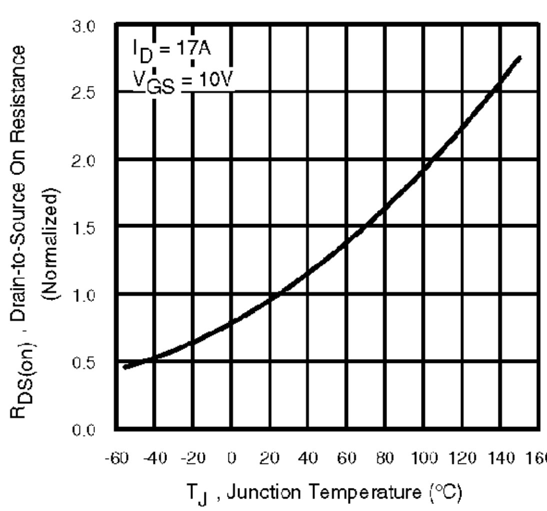


Fig 4. Normalized On-Resistance Vs. Temperature

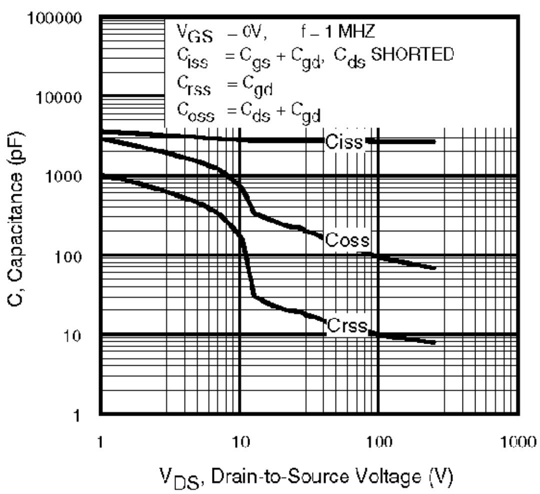


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

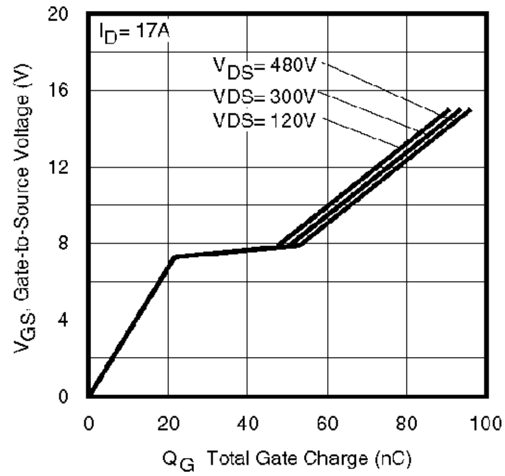


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

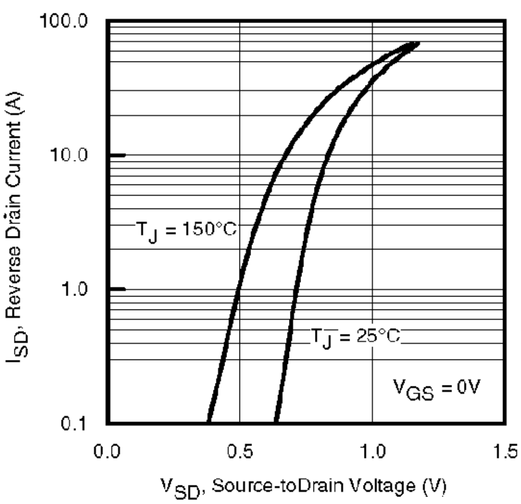


Fig 7. Typical Source-Drain Diode Forward Voltage

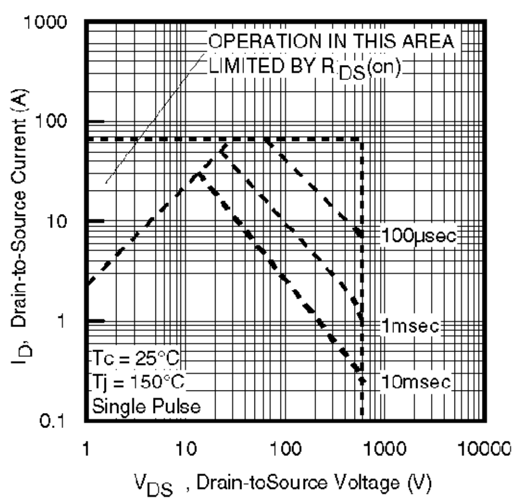


Fig 8. Maximum Safe Operating Area

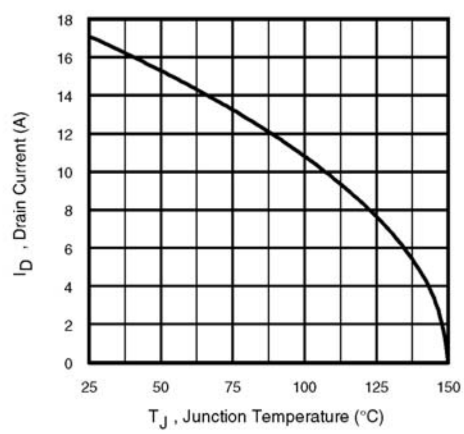


Fig 9. Maximum Drain Current Vs. Case Temperature

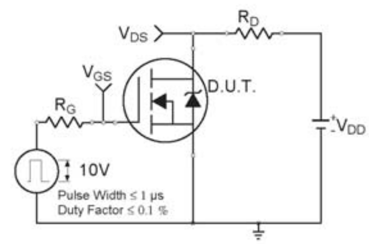


Fig 10a. Switching Time Test Circuit

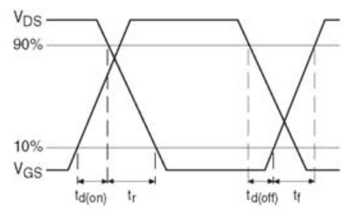


Fig 10b. Switching Time Waveforms

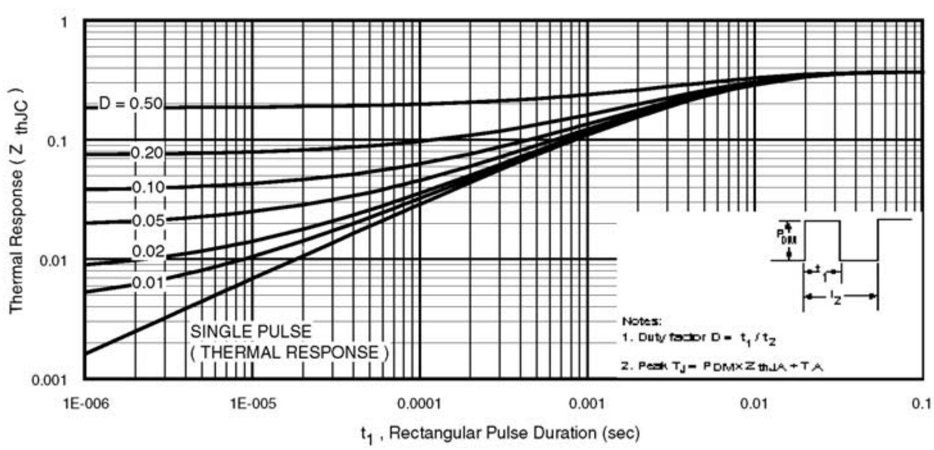


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

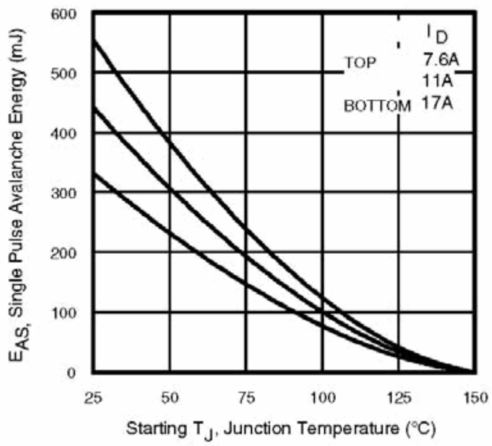


Fig 12a. Maximum Avalanche Energy Vs. Drain Current

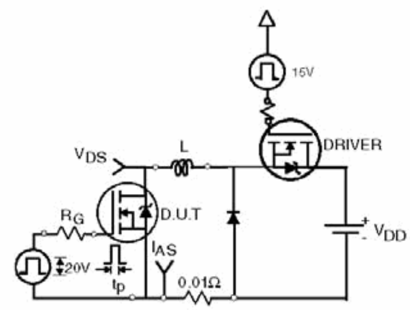


Fig 12c. Unclamped Inductive Test Circuit

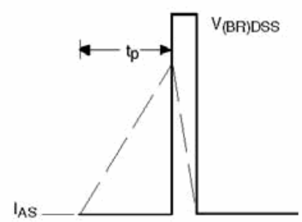


Fig 12d. Unclamped Inductive Waveforms

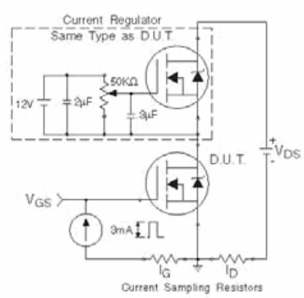


Fig 13a. Gate Charge Test Circuit

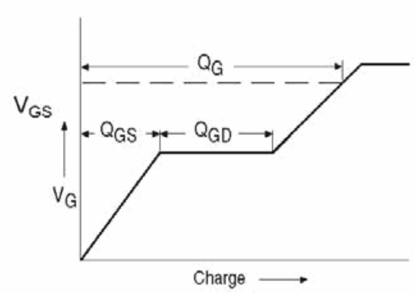
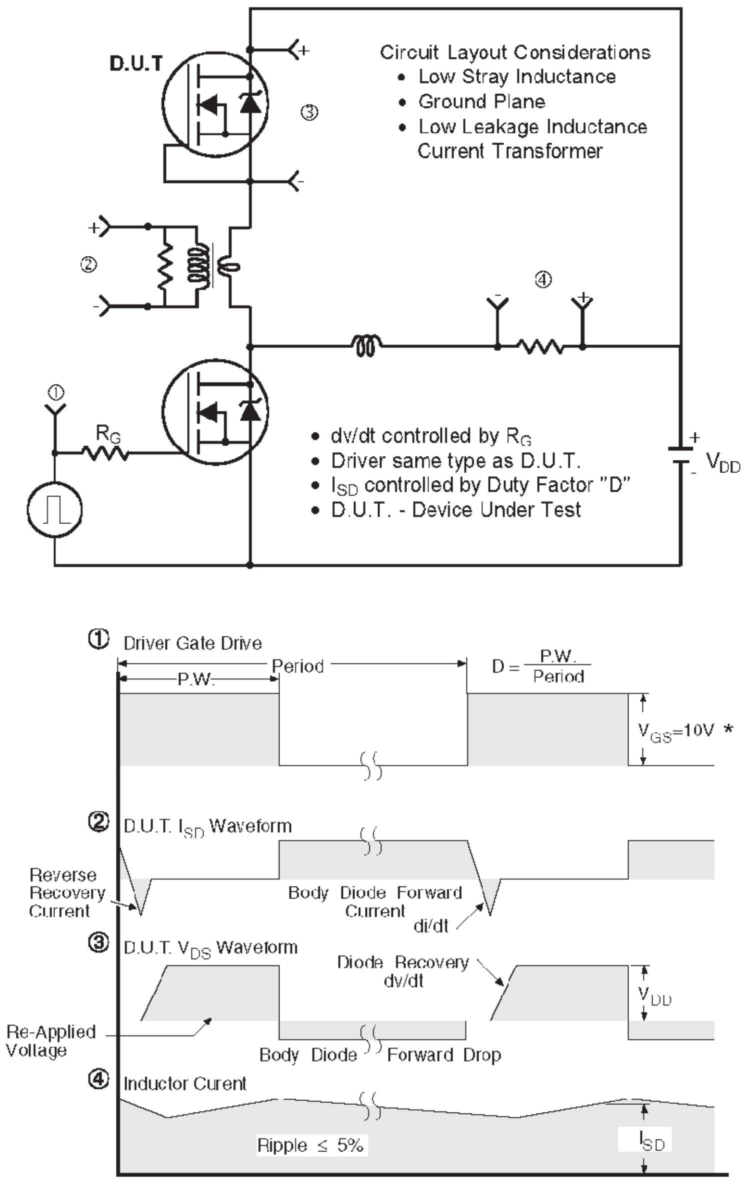


Fig 13b. Basic Gate Charge Waveform

Peak Diode Recovery dv/dt Test Circuit

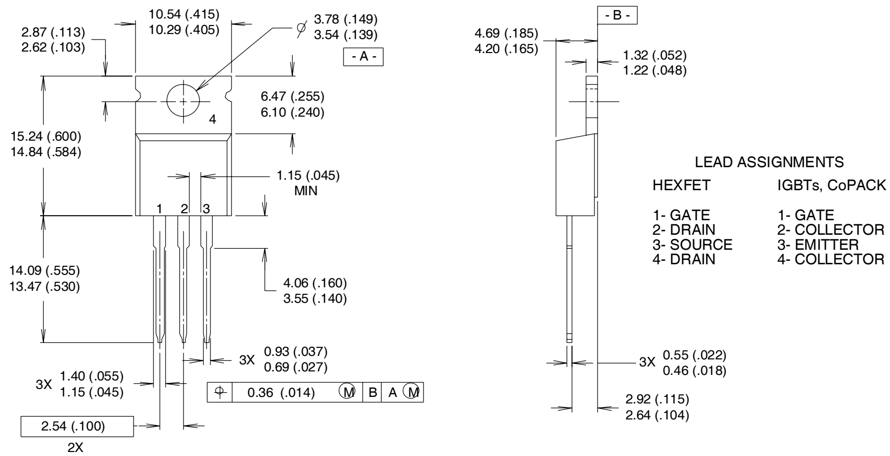


* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFET® Power MOSFETs

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.

2 CONTROLLING DIMENSION : INCH

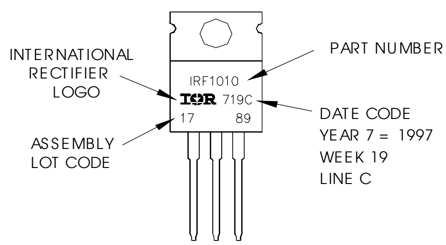
3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.

4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



TO-220AB package is not recommended for Surface Mount Application

Data and specifications subject to change without notice.
This product has been designed and qualified for the Automotive [Q101] market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
08/04

Notice

The products described herein were acquired by Vishay Intertechnology, Inc., as part of its acquisition of International Rectifier's Power Control Systems (PCS) business, which closed in April 2007. Specifications of the products displayed herein are pending review by Vishay and are subject to the terms and conditions shown below.

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.

International Rectifier®, IR®, the IR logo, HEXFET®, HEXSense®, HEXDIP®, DOL®, INTERO®, and POWIRTRAIN® are registered trademarks of International Rectifier Corporation in the U.S. and other countries. All other product names noted herein may be trademarks of their respective owners.